

CLAIM LISTING:

1. (Previously Cancelled)
2. (Previously Cancelled)
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6. (Previously Cancelled)
7. (Previously Cancelled)
8. (Previously Cancelled)

*Sep 15 / 2003*  
*entered by*  
*Sep 23 / 2003*

9. (Previously Amended) A method of fabricating a semiconductor device, comprising:  
preparing a semiconductor substrate;  
forming a silicon oxide layer on the semiconductor substrate;  
forming a conductive layer on the silicon oxide layer; and  
forming a metal oxide layer with a substantially uniform thickness at an interface between the silicon oxide layer and the conductive layer.

10. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming a silicon oxide layer further comprises forming a silicon dioxide layer having a thickness of 10 to 100Å.

11. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming the conductive layer further comprises forming a metal layer or a metal nitride layer.

12. (Original) A method of fabricating a semiconductor device according to claim 11, wherein the step of forming the metal layer further comprises forming a layer of at least one metal selected from a group consisting of tungsten (W), tantalum (Ta), titanium (Ti), and aluminum (Al).

13. (Original) A method of fabricating a semiconductor device according to claim 11, wherein the step of forming the metal nitride layer further comprises forming a layer of at least one metal nitride selected from a group consisting of tungsten nitride (WN), tantalum nitride (TaN), titanium nitride (TiN) and aluminum nitride (AlN).

14. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming the conductive layer further comprises forming a conductive layer having a thickness of 100 to 2000Å.

15. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming a metal oxide layer at an interface between the silicon oxide layer and the conductive layer further comprises a thermal treatment, the thermal treatment being conducted at a temperature of 500 to 1000C and under an inert gas ambient.

16. (Original) A method of fabricating a semiconductor device according to claim 15, wherein the inert gas comprises at least one gas selected from a group consisting of nitrogen (N), argon (Ar), and helium (He).

17. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming a metal oxide layer further comprises forming a metal oxide layer having a dielectric constant of at least 3.9.

18. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the step of forming a metal oxide layer further comprises oxidizing a portion of the metal layer with oxygen atoms from the silicon oxide layer.

19. (Original) A method of fabricating a semiconductor device according to claim 9, wherein the silicon oxide layer is a gate insulator and the conductive layer is a gate electrode.